



ABSTRACT OF THE DISCLOSURE

A dynamic random access memory or the like, in which in order to prevent the breakdown voltage deterioration of a capacitive element when a TiN film
5 of an electrode material is deposited by the CVD method over a tantalum film constituting the capacitor insulating film of the capacitive element, a passivation film is formed in advance over the surface of the tantalum oxide film to prevent the tantalum
10 oxide film from contacting with a nitrogen-containing reducing gas, when the TiN film is deposited over the tantalum oxide film by the CVD method using a titanium-containing source gas and the nitrogen-containing reducing gas.

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